Transistor NPN, TO-3





Description:

Complementary silicon power transistors.

The MJ15003 power transistors designed for high power audio, disk head positioners and other linear applications.

Features:

- · High safe operating area (100% tested) 5A at 50V
- · For low distortion complementary designs
- High DC current gain hFE = 25 (minimum) at IC = 5A DC
- · Pb-free package

Maximum Ratings (Note 1)

| Rating | Symbol | Value | Unit |
|---|----------|-------------|--------|
| Collector-Emitter Voltage | VCEO | 140 | V DC |
| Collector-Base Voltage | Vсво | 140 | |
| Emitter-Base Voltage | VEBO | 5 | |
| Collector Current - Continuous | Ic | 20 | A DC |
| Base Current - Continuous | Ів | 5 A DC | |
| Emitter Current - Continuous | lε | 25 | |
| Total Device Dissipation at TC = 25°C Derate above 25°C | Po | 250 1.43 | W W/°C |
| Operating and Storage Junction Temperature Range | TJ, Tstg | -65 to +200 | °C |





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Thermal Characteristics

| Characteristics | Symbol | Max. | Unit |
|---|----------------|------|------|
| Thermal Resistance, Junction-to-Case | $R_{	heta JC}$ | 0.7 | °C/W |
| Maximum Lead Temperature for Soldering Purpose 1/6 inches from Case for ≤10 Seconds | TL | 265 | °C |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

Electrical Characteristics (Tc = 25°C unless otherwise noted)

| Characteristic | Symbol | Min. | Max. | Unit |
|--|----------------------|--------|----------|----------------|
| Off Characteristics | | | | |
| Collector-Emitter Sustaining Voltage (Note 1) $(I_C = 200 \text{mA DC}, I_B = 0)$ | V _{EO(sus)} | 140 | - | V DC |
| Collector Cut off Current (V_{CE} = 140V DC, $V_{BE (off)}$ = 1.5V DC) (V_{CE} = 140V DC, $V_{BE (off)}$ = 1.5V DC, V_{CE} = 150°C) | I _{CEX} | - | 100 2 | μΑ DC mA DC |
| Collector Cut off Current $(V_{CE} = 140V DC, I_B = 0)$ | I _{CEO} | - | 250 | 4.00 |
| Emitter Cut off Current $(V_{EB} = 5V \text{ dc } I_C = 0)$ | I _{EBO} | - | 100 | - μA DC |
| Second Breakdown | | | | |
| Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 50V DC, t = 1s (non repetitive)) (V_{CE} = 100V DC, t = 1s (non repetitive)) | I _{S/b} | 5 1 | - | A DC |
| On Characteristic | | | | |
| DC Current Gain (I _C = 5A DC, V _{CE} = 2V DC) | hfe | 25 | 150 | - |
| Collector-Emitter Saturation Voltage $(I_C = 5A DC, I_B = 0.5A DC)$ | VCE (sat) | - | 1 | V DC |
| Base-Emitter On Voltage (I _C = 5A DC, V _{CE} = 2V DC) | VBE (on) | - | 2 | |
| Dynamic Characteristics | | | • | |
| Current-Gain - Bandwidth Product ($I_C = 0.5ADC$, $V_{CE} = 10VDC$, $f_{test} = 0.5MHz$) | fτ | 2 | | MHz |
| Output Capacitance $(V_{CB} = 10V DC, I_{E} = 0, f_{test} = 1MHz)$ | Cob | - | 1,000 | pF |

^{1.} Pulse Test : Pulse Width = 300µs, Duty Cycle ≤2%.

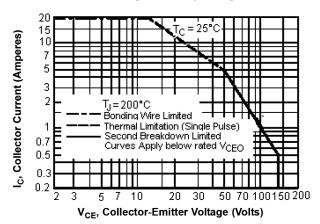




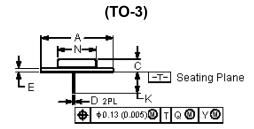
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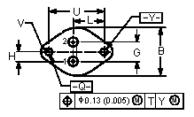


Active - Region Safe Operating Area



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate Ic - VcE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than curves indicate. The data is based on TJ (PK) = 200° C; Tc is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values.





Style 1: Pin 1. Base 2. Emitter Collector (Case)

| Dimensions | Minimum | Maximum | |
|------------|------------------------|--------------|--|
| А | 1.55 (39.37) Reference | | |
| В | - | 1.05 (26.67) | |
| С | 0.25 (6.35) | 0.335 (8.51) | |
| D | 0.038 (0.97) | 0.043 (1.09) | |
| E | 0.055 (1.4) | 0.07 (1.77) | |
| G | 0.43 (10.92) BSC | | |
| Н | 0.215 (5.46) BSC | | |
| K | 0.44 (11.18) | 0.48 (12.19) | |
| L | 0.665 (16.89) BSC | | |
| N | - | 0.83 (21.08) | |
| Q | 0.151 (3.84) | 0.165 (4.19) | |
| U | 1.187 (30.15) BSC | | |
| V | 0.131 (3.33) | 0.188 (4.77) | |

Dimensions: Millimetres

Part Number Table

| Description | Part Number |
|-----------------------|-------------|
| Transistor, NPN, TO-3 | MJ15003 |

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